Changjiang

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

M8550 TRANSISTOR (PNP)

FEATURES

Power dissipation

 P_{CM} : 0.625 W (Tamb=25)

Collector current

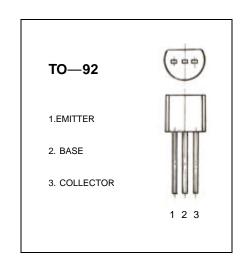
I_{CM} : -1 A

Collector-base voltage

 $V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150



ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	lc= -100 μ A , l _E =0	-40		V
Collector-emitter breakdown voltage	V(BR) _{CEO} *	I _C = -0.1mA , I _B =0	-25		V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = -100 μ A , I _C =0	-6		V
Collector cut-off current	Ісво	V _{CB} = -35V , I _E =0		-0.1	μА
Collector cut-off current	I _{CEO}	V _{CE} = -20V , I _B =0		-0.1	μА
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-5mA	45		
	h _{FE(2)}	V _{CE} =-1V, I _C =-100mA	85	300	
	h _{FE (3)}	V _{CE} =-1V, I _C =-800mA	40		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -800mA, I _B =-80mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA		-1.2	V
Transition frequency	f _T	V _{CE} =-6V, I _C = -20mA f=30MHz	150		MHz

^{*} Pulse Test: pulse width 300µs, duty cycle 2%。